

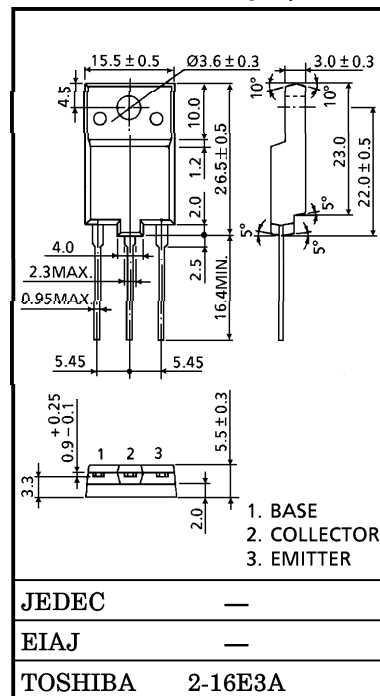
TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED MESA TYPE

2SC5588

HORIZONTAL DEFLECTION OUTPUT FOR SUPER HIGH RESOLUTION DISPLAY, COLOR TV FOR MULTI-MEDIA & HDTV
HIGH SPEED SWITCHING APPLICATIONS

Unit in mm

- High Voltage : $V_{CB0} = 1700\text{ V}$
- Low Saturation Voltage : $V_{CE(sat)} = 3\text{ V (Max.)}$
- High Speed : $t_f(2) = 0.1\ \mu\text{s (Typ.)}$



Weight : 5.5 g (Typ.)

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CB0}	1700	V
Collector-Emitter Voltage		V_{CEO}	800	V
Emitter-Base Voltage		V_{EBO}	5	V
Collector Current	DC	I_C	15	A
	Pulse	I_{CP}	30	
Base Current		I_B	7.5	A
Collector Power Dissipation ($T_c = 25^\circ\text{C}$)		P_C	75	W
Junction Temperature		T_j	150	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	-55~150	$^\circ\text{C}$

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Collector Cut-off Current	I_{CBO}	$V_{CB} = 1700 \text{ V}, I_E = 0$	—	—	1	mA	
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 5 \text{ V}, I_C = 0$	—	—	100	μA	
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10 \text{ mA}, I_B = 0$	800	—	—	V	
DC Current Gain	$h_{FE(1)}$	$V_{CE} = 5 \text{ V}, I_C = 2 \text{ A}$	22	—	45	—	
	$h_{FE(2)}$	$V_{CE} = 5 \text{ V}, I_C = 9 \text{ A}$	6.5	—	12		
	$h_{FE(3)}$	$V_{CE} = 5 \text{ V}, I_C = 12 \text{ A}$	4.8	—	8.0		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 12 \text{ A}, I_B = 3 \text{ A}$	—	—	3	V	
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 12 \text{ A}, I_B = 3 \text{ A}$	—	1.0	1.5	V	
Transition Frequency	f_T	$V_{CE} = 10 \text{ V}, I_C = 0.1 \text{ A}$	—	2	—	MHz	
Collector Output Capacitance	C_{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	—	240	—	pF	
Switching Time	Storage Time	$t_{stg(1)}$	$I_{CP} = 9 \text{ A}, I_{B1}(\text{end}) = 1.1 \text{ A}$ $f_H = 32 \text{ kHz}$	—	3.5	4	μs
	Fall Time	$t_f(1)$		—	0.25	0.35	
	Storage Time	$t_{stg(2)}$	$I_{CP} = 6.5 \text{ A}, I_{B1}(\text{end}) = 1 \text{ A}$ $f_H = 100 \text{ kHz}$	—	1.8	2	μs
	Fall Time	$t_f(2)$		—	0.1	0.15	

